

IN THE CLAIMS:

Claims 51 through 82 were previously cancelled. Claims 1, 4-9, 13, 17, 21-26, 33, 34, 40, 44, 45 and 47 have been amended herein. All of the pending claims 1 through 50 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Currently amended) An interposer apparatus for use between a first semiconductor device and a second semiconductor device, said first semiconductor device and said second semiconductor device each having a plurality of bond pads disposed on an active surface thereof and a bottom surface, comprising:  
a first surface having a first length, a first width, and a coefficient of thermal expansion and a second surface having a length, a width smaller than said first width of said first surface, and a coefficient of thermal expansion substantially the same as the coefficient of thermal expansion of the first surface, said first surface comprising an overhang portion of said interposer apparatus for protection of said plurality of bond pads disposed on said first semiconductor device and said second surface being mountable to said active surface of said first semiconductor device.
2. (Original) The interposer apparatus according to claim 1, wherein said overhang portion further comprises at least one conductive strip for connection to at least one bond pad of said plurality of bond pads of said first semiconductor device.
3. (Original) The interposer apparatus according to claim 1, wherein said first and second surfaces are formed from a common unitary member.

4. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides thermal conductivity for thermal energy transfer from said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

5. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides thermal insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

6. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides one of thermal conductivity and thermal insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

7. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides electrical insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

8. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides thermal insulation and electrical insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

9. (Currently amended) The interposer apparatus according to claim 1, wherein said interposer apparatus provides thermal conductivity and electrical insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

10. (Previously presented) The interposer apparatus according to claim 3, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device.

11. (Previously presented) The interposer apparatus according to claim 3, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said second semiconductor device.

12. (Previously presented) The interposer apparatus according to claim 3, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device and said second semiconductor device.

13. (Currently amended) The interposer apparatus according to claim 1, wherein said first surface of said interposer apparatus is connected to a base portion of said second semiconductor device.

14. (Original) The interposer apparatus according to claim 1, wherein a third semiconductor device is mounted adjacent said second semiconductor device.

15. (Previously presented) The interposer apparatus according to claim 1, wherein said length of said second surface is substantially the same as said first length of said first surface.

16. (Previously presented) The interposer apparatus according to claim 1, wherein said length of said second surface is substantially the same as the width of said second surface.

17. (Currently amended) An interposer apparatus for use between a first semiconductor device and a second semiconductor device, said first semiconductor device and said second semiconductor device each having a plurality of bond pads on an active surface thereof and a bottom surface, said interposer apparatus comprising:

- a first surface having a first length, a first width, a coefficient of thermal expansion;
- a second surface having a length, a width smaller than said first width of said first surface, and a coefficient of thermal expansion substantially the same as the coefficient of thermal expansion of the first surface, said first surface comprising an overhang portion of said interposer apparatus for protection of said plurality of bond pads disposed on said first semiconductor device and said second surface being mountable to said active surface of said first semiconductor device;
- a third surface having a first length and a first width; and
- a fourth surface having a length and a width smaller than said first width of said third surface, said third surface providing an overhang portion of said interposer apparatus for protection of said plurality of bond pads disposed on said second semiconductor device and said fourth surface being mountable to said active surface of said second semiconductor device.

18. (Original) The interposer apparatus according to claim 17, wherein said overhang portion further comprises at least one conductive strip for connection to at least one bond pad of said plurality of bond pads of said first semiconductor device.

19. (Original) The interposer apparatus according to claim 17, wherein said first and second surfaces are formed from a common unitary member.

20. (Original) The interposer apparatus according to claim 17, wherein said third and fourth surfaces are formed from a common unitary member.

21. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides thermal conductivity for thermal energy transfer from said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

22. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides thermal insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

23. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides one of thermal conductivity and thermal insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

24. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides electrical insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

25. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides thermal insulation and electrical insulation between said first semiconductor device and said second semiconductor device, each mounted to said interposer apparatus.

26. (Currently amended) The interposer apparatus according to claim 17, wherein said interposer apparatus provides thermal conductivity and electrical insulation between said first semiconductor device and said second semiconductor device mounted to said interposer apparatus.

27. (Previously presented) The interposer apparatus according to claim 19, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device.

28. (Previously presented) The interposer apparatus according to claim 20, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device.

29. (Previously presented) The interposer apparatus according to claim 19, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said second semiconductor device.

30. (Previously presented) The interposer apparatus according to claim 20, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said second semiconductor device.

31. (Previously presented) The interposer apparatus according to claim 19, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device and said second semiconductor device.

32. (Previously presented) The interposer apparatus according to claim 20, wherein said common unitary member has a coefficient of thermal expansion substantially equal to that of said first semiconductor device and said second semiconductor device.

33. (Currently amended) The interposer apparatus according to claim 17, wherein said first surface of said interposer apparatus is connected to a base portion of said second semiconductor device.

34. (Currently amended) The interposer apparatus according to claim 17, wherein said third surface of said interposer apparatus is connected to a base portion of a third semiconductor device.

35. (Original) The interposer apparatus according to claim 17, wherein a third semiconductor device is mounted adjacent said second semiconductor device.

36. (Previously presented) The interposer apparatus according to claim 17, wherein said length of said second surface is substantially the same as said first length of said first surface.

37. (Previously presented) The interposer apparatus according to claim 17, wherein said length of said second surface is substantially the same as the width of said second surface.

38. (Previously presented) The interposer apparatus according to claim 17, wherein said length of said fourth surface is substantially the same as said first length of said third surface.

39. (Previously presented) The interposer apparatus according to claim 17, wherein said length of said fourth surface is substantially the same as the width of said fourth surface.

40. (Currently amended) An interposer apparatus for use between a plurality of semiconductor devices, each semiconductor device of said plurality of semiconductor devices having at least one bond pad on an active surface thereof and a bottom surface, comprising: a first surface having a first length, a first width, and a coefficient of thermal expansion;

a second surface having a length, a width smaller than said first width of said first ~~surface, a and surface, and a~~ coefficient of thermal expansion substantially the same as the coefficient of thermal expansion of the first surface, said first surface providing a protective overhang portion that protects the at least one bond pad on an active surface of a first semiconductor device and said second surface being mountable to said active surface of said first semiconductor device.

41. (Previously presented) The interposer apparatus according to claim 40, wherein said protective overhang portion further comprises at least one conductive strip for connecting to said first semiconductor device.

42. (Original) The interposer apparatus according to claim 40, wherein said first and second surfaces are formed from a unitary member.

43. (Previously presented) The interposer apparatus according to claim 40, further comprising:  
a third surface having a first length and a first width; and  
a fourth surface having a length and a width smaller than said first width of said third surface, said third surface providing a portion that is at least partially covering said at least one bond pad on an active surface of a second semiconductor device and said fourth surface being mountable to said active surface of said second semiconductor device.

44. (Currently amended) The interposer apparatus according to claim 40, wherein said interposer apparatus provides thermal and electrical insulation between said first semiconductor device and a second semiconductor device of said plurality of semiconductor devices connected to said interposer apparatus.



45. (Currently amended) The interposer apparatus according to claim 40, wherein said interposer apparatus provides thermal conductivity and electrical insulation between said first semiconductor device and a second semiconductor device of said plurality of semiconductor devices connected to said interposer apparatus.

46. (Original) The interposer apparatus according to claim 42, wherein said unitary member has a coefficient of thermal expansion substantially the same as said first semiconductor device.

47. (Currently amended) The interposer apparatus according to claim 40, wherein said first surface of said interposer apparatus is connected to a base portion of a second semiconductor device of said plurality of semiconductor devices.

48. (Original) The interposer apparatus according to claim 47, wherein at least a third semiconductor device mounts adjacent said second semiconductor device of said plurality of semiconductor devices.

49. (Previously presented) The interposer apparatus according to claim 40, wherein said length of said second surface is substantially the same as said first length of said first surface.

50. (Previously presented) The interposer apparatus according to claim 40, wherein said length of said second surfaces is substantially the same as the width of said second surface.

51.-82. (Cancelled)